This GIDEP PCN is to announce a change in the electrical characteristics for the following International Rectifier Part No listed below. This change is also coordinated with MIL-PRF-19500/698 change from revision E to F.

**IRHMS57160 (JANSR2N7471T1)**

100V 100kRad Hi-Rel Single N-Channel TID Hardened MOSFET in a Low Ohmic TO-254AA package

Electrical Characteristics @ $T_j = 25^\circ C$,
- $R_{DS(on)}$ [Static Drain-to-Source On-State Resistance], with test condition of $V_{GS} = 12V$, $I_D = 45A$
  - Change $R_{DS(on)}$ Max limit from $0.013 \Omega$ to $0.014 \Omega$

Table 1. Electrical Characteristics @ $T_j = 25^\circ C$, Post Total Dose Irradiation
- $R_{DS(on)}$ [Static Drain-to-Source On-State Resistance], with test condition of $V_{GS} = 12V$, $I_D = 45A$
  - For up to 500K Rads(Si), Low-Ohmic TO-254 only
    - Change $R_{DS(on)}$ Max limit from $0.013 \Omega$ to $0.014 \Omega$
  - For 1000K Rads (Si), Low-Ohmic TO-254 only
    - Change $R_{DS(on)}$ Max limit from $0.014 \Omega$ to $0.015 \Omega$

Reference: IR Datasheet PD-95889